A 17–95.6 TOPS/W Deep Learning Inference Accelerator with Per-Vector Scaled 4-bit Quantization for Transformers in 5nm

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Abstract

We present a deep neural network (DNN) accelerator designed for efficient execution of transformer-based DNNs, which have become ubiquitous for natural language processing tasks. DNN inference accelerators often employ specialized hardware techniques such as reduced precision to improve energy efficiency, but many of these techniques result in catastrophic accuracy loss on transformers. The proposed accelerator supports per-vector scaled quantization and approximate softmax to enable the use of 4-bit arithmetic with little accuracy loss. The 5nm prototype achieves 95.6 TOPS/W in benchmarking and 1711 inferences/s/W with only 0.7% accuracy loss on BERT, demonstrating a practical accelerator design for energy-efficient inference with transformers.

Keywords: DNN inference accelerator, BERT, transformers.

Introduction

Deep neural networks (DNNs) using attention-based transformer architectures have seen significant interest due to their superior performance in natural language processing [1] and vision tasks [2]. These trends suggest that transformers will become an increasingly common workload across a wide range of applications, making them an important target for hardware specialization to improve performance and energy efficiency. We present a DNN inference accelerator that includes specialized capabilities targeting transformers, enabling high energy efficiency while maintaining high task accuracy.

Accelerating Transformers

Reducing arithmetic precision is a common technique to improve energy efficiency on DNN workloads [3], as it reduces the cost of both multiply-accumulate (MAC) operations and data movement. However, reduced-precision math introduces quantization error, which can cause loss of task accuracy. Traditional quantization techniques that enable 4b math on small networks fail catastrophically when applied to more sophisticated transformer networks, and attention layers in transformers differ significantly from convolution layers in their shape and types of computations (see Fig.1).

The inference accelerator presented in this work uses pervector scaled quantization (VSQ) to enable energy-efficient 4b math while maintaining task accuracy on transformers [4]. In addition to applying a coarse-grained scale factor for each output column, VSQ applies a scale factor at vector granularity within each input matrix (see Fig.2). When input vectors are multiplied, their 8b scale factors are multiplied to scale the result. VSQ enables low-precision arithmetic with reduced quantization error and minimal hardware overhead (see Fig.3).

Transformers include non-linear operations such as softmax and GELU, which are expensive in hardware. This work implements a hardware-friendly softmax approximation that uses base 2 instead of base e, low-precision fixed-point data formats, and online normalization to reduce data movement [5], greatly reducing hardware cost with minimal impact on accuracy (see Fig.4). GELU is replaced with the simpler ReLU operation.

Deep Learning Inference Accelerator

Fig.5 shows a block diagram of the accelerator, which contains 16 vector lanes, each of which implements independent 8b and 4b datapaths. Each lane performs a 64-element (32-element for 8b) multiply followed by an accumulating sum each cycle, as well as a scale factor multiplication to implement VSQ. The accelerator contains 132KB of SRAM storage for input matrices A and B. After accumulation is complete, a postprocessing unit (PPU) optionally performs operations such as ReLU, approximate softmax, bias addition, and scaling. Final results are stored in an 8.5KB output memory.

The accelerator minimizes expensive SRAM reads by employing an output-stationary, local-A-stationary dataflow [6] (see Fig.6). A-matrix inputs are read out of the A-buffer once every 16 cycles and stored in a register for temporal reuse. B-matrix inputs are read once each cycle and reused across the 16 lanes. 24b partial sums are temporally accumulated in a 16entry latch array before sending the completed sum to the PPU. This process is repeated to compute the output matrix by reusing A-matrix and B-matrix inputs. The accelerator can compute matrix multiply, convolution, and fully connected layers of different sizes by configuring the SRAM address generators. Buffer managers enable the pipelining of computation with the streaming of input data. The accelerator could be tiled spatially to compose a larger system.

Measurement Results

The 0.15mm² accelerator is fabricated in a TSMC 5nm process. Fig.7 shows the measured energy efficiency of the accelerator under different operating conditions and input densities. The system achieves 95.6 TOPS/W with 50%-dense 4b input matrices and VSQ enabled. VSQ imposes a 0.8% energy efficiency overhead compared to 4b math with per-matrix scaling with 50% non-zero inputs at 0.67V. Table 1 shows achieved performance, energy efficiency, and task accuracy on a variety of workloads. Quantization-aware fine-tuning is applied to pretrained FP32 weights, enabling $\leq 1.1\%$ accuracy loss on BERT when VSQ is enabled. Without VSQ, 4b inference for transformers results in unacceptable accuracy loss even when retraining techniques are applied. The system achieves 1711 inferences/s/W running BERT-Base with a sequence length of 128 on SQuAD. Table 2 presents a comparison with prior work. Fig.8 shows an annotated die micrograph.

Conclusion

The presented system achieves 2.2-5.8X better energy efficiency and 4-16X better area efficiency than prior work. Unlike many prior proposals to improve energy efficiency, VSQ and approximate softmax allow the accelerator to maintain task accuracy on cutting-edge DNN workloads.

References

A. Vaswani et al., NeurIPS, 2017. [2] A. Dosovitskiy et al., ICLR,
2021. [3] A. Agrawal et al., ISSCC, 2021. [4] S. Dai et al., MLSys,
2021. [5] J. Stevens et al., DAC, 2021. [6] R. Venkatesan et al.,
ICCAD, 2019. [7] H. Mo et al., ISSCC, 2021. [8] J-S. Park et al.,
ISSCC, 2021. [9] C. Lin et al., ISSCC, 2020.

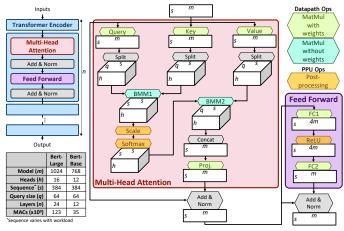


Fig.1: Workload components of transformers.

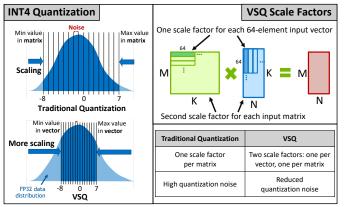


Fig.2: Per-vector scaled quantization (VSQ).



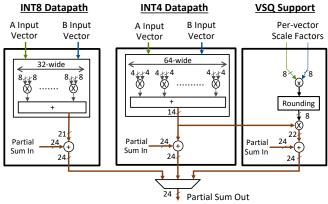
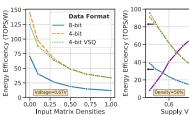
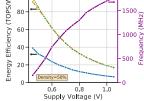


Fig.3: 8b/4b datapath with VSQ support.





Process Technology

Supply Voltage (V)

Frequency (MHz)

Data Formats

On-Chip SRAM (KB)

Performance (TOPS)

Area (mm²)

(ZHM

LPO1

[3]

7nm

19.6

0.55 - 0.75

1000 - 1600

8192

102.4 (4b, 0.75V)

INT2/4, FP8/16/3

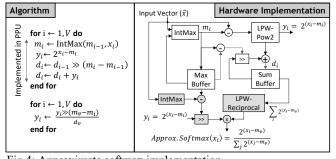


Fig.4: Approximate softmax implementation.

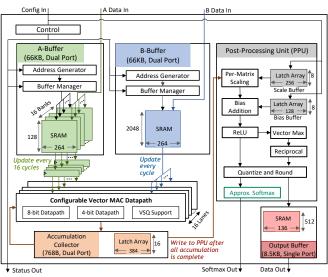


Fig.5: Accelerator block diagram.

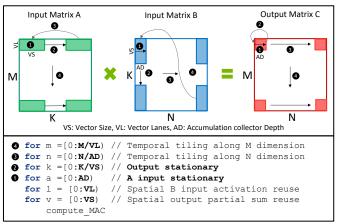


Fig.6: Workload mapping and data reuse.

Table 2: Comparison to prior work.

[8]

5nm

5.46

0.55 – 0.9

332 – 1196

3072

INT8, INT16

14.7 (8b, 0.9V)

Table 1:	Measured	l application	performance	at 0.67V.

Dataset, Task	SQuAD v1.1, Reading Comprehension								ImageNet, Image Classification									
Network	BERT-Base				BERT-Large					DeIT-Small			DeIT-Base					
Sequence Length	128		384		128		384		197			197						
Baseline FP32 Accuracy (%)	87.5		87.5		90.3		90.9		79.8			81.8						
Data Bitwidth (4V = 4b VSQ)	4b	4V	8b	4b	4V	8b	4b	4V	8b	4b	4V	8b	4b	4V	8b	4b	4V	8b
Accuracy Loss (%)	80	0.7	0.7	81	0.5	0	88	1.1	1.1	89	0.8	0.1	29	3.6	0.7	25	1.3	0.4
MAC Utilization (%)	-	98	99	-	98	99	-	98	99	-	98	99	-	94	96	-	97	98
Throughput (inferences/s)	-	88	45	-	28	14	-	25	13	-	8.1	4.1	-	210	108	-	56	28
Energy Eff. (inferences/s/W)	-	1.7k	745	-	539	235	-	502	216	-	160	69	-	3.5k	1.5k	-	1.0k	406

[9]

7nm

3.04

0.58 – 0.83

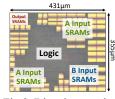
290 - 880

2176

INT8/16, FP16

3.6 (8b, 0.83V)

Fig.7: Chip measurements.



Energy Efficiency (TOPS/W) 16.5* (4b, 0.55V) 17.5* (8b, 0.6V) 13.6* (8b, 0.6V) 6.8* (8b, 0.58V) Area Efficiency (TOPS/mm²) 5.22 (4b. 0.75V) 0.75 (8b. 0.9V) 2.69 (8b, 0.9V) 1.2 (8b, 0.83V)

Fig.8: Die micrograph.

[7]

28nm

1.9

0.6 - 0.9

100 - 470

206

INT8

1.43 (8b, 0.9V)

INT4

3.6 (1.05V)

91.1⁺ (0.46V)

23.3 (1.05V)

This work

5nm

0.153

0.46 - 1.05

152 – 1760

141

INT4 VSC

3.6 (1.05V)

95.6⁺ (0.46V)

23.3 (1.05V)

INT8

1.8 (1.05V)

39.1⁺ (0.46V)

11.7 (1.05V

Input densities not reported. * Measured with 50% non-zero input densities. Includes estimated leakage power